

N-Channel Enhancement Mode MOSFET

Feature

30V/5.8A, $R_{DS(ON)} = 23m\Omega(MAX)$ @ $V_{GS} = 10V$.

$R_{DS(ON)} = 28m\Omega(MAX)$ @ $V_{GS} = 4.5V$.

$R_{DS(ON)} = 34m\Omega(MAX)$ @ $V_{GS} = 2.5V$.

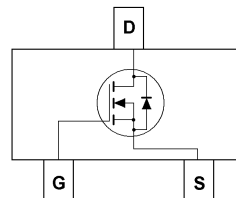
Super High dense cell design for extremely low $R_{DS(ON)}$.

Reliable and Rugged.

SOT-23 for Surface Mount Package.



SOT-23



Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings $T_A = 25^\circ C$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	5.8	A

Electrical Characteristics $T_A = 25^\circ C$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=12V, V_{DS}=0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-12V, V_{DS}=0V$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.6	0.9	1.5	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=4A$	-	23	28	$m\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	28	33	$m\Omega$
		$V_{GS}=2.5V, I_D=2A$	-	34	52	$m\Omega$

Package Outline Dimensions (UNIT: mm)

SOT-23

